

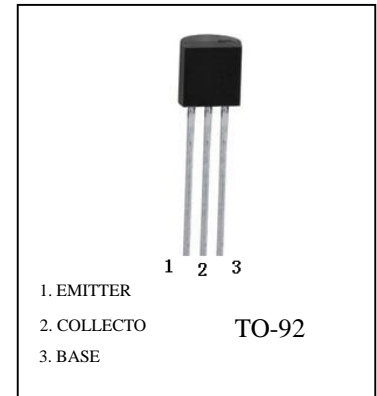
**FEATURES**

Power dissipation

MARKING:A1015

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-150	mA
Collector Power Dissipation	$P_C$	400	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55-150	°C

**A1015 (PNP)**


ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Pyp	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -50V, I_B = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -6V, I_C = -2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1.1	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -1mA, F = 30MHz$	80			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$			7	pF
Noise Figure	NF	$V_{CE} = -6V, I_C = -0.1mA, f$			6	dB

## CLASSIFICATION OF HFE

Rank	O	Y	GR
Range	70-140	120-240	200-400

A1015 Typical Characteristics

